# E·XFL

## Intel - EP20K200CQ240C8 Datasheet



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#### Understanding <u>Embedded - FPGAs (Field</u> <u>Programmable Gate Array)</u>

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

## **Applications of Embedded - FPGAs**

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

#### Details

Product Status	Obsolete
Number of LABs/CLBs	832
Number of Logic Elements/Cells	8320
Total RAM Bits	106496
Number of I/O	168
Number of Gates	526000
Voltage - Supply	1.71V ~ 1.89V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	240-BFQFP
Supplier Device Package	240-PQFP (32x32)
Purchase URL	https://www.e-xfl.com/product-detail/intel/ep20k200cq240c8

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

The LAB-wide control signals can be generated from the LAB local interconnect, global signals, and dedicated clock pins. The inherent low skew of the FastTrack interconnect enables it to be used for clock distribution. Figure 4 shows the LAB control signal generation circuit.



#### Figure 4. LAB Control Signal Generation

#### Notes to Figure 4:

- The LABCLR1 and LABCLR2 signals also control asynchronous load and asynchronous preset for LEs within the LAB.
- (2) The SYNCCLR signal can be generated by the local interconnect or global signals.

## Logic Element

The LE, the smallest unit of logic in the APEX 20KC architecture, is compact and provides efficient logic usage. Each LE contains a four-input LUT, which is a function generator that can quickly implement any function of four variables. In addition, each LE contains a programmable register and carry and cascade chains. Each LE drives the local interconnect, MegaLAB interconnect, and FastTrack interconnect routing structures. See Figure 5. The APEX 20KC architecture provides two types of dedicated high-speed data paths that connect adjacent LEs without using local interconnect paths: carry chains and cascade chains. A carry chain supports high-speed arithmetic functions such as counters and adders, while a cascade chain implements wide-input functions such as equality comparators with minimum delay. Carry and cascade chains connect LEs 1 through 10 in an LAB and all LABs in the same MegaLAB structure.

## Carry Chain

The carry chain provides a very fast carry-forward function between LEs. The carry-in signal from a lower-order bit drives forward into the higherorder bit via the carry chain, and feeds into both the LUT and the next portion of the carry chain. This feature allows the APEX 20KC architecture to implement high-speed counters, adders, and comparators of arbitrary width. Carry chain logic can be created automatically by the Quartus II Compiler during design processing, or manually by the designer during design entry. Parameterized functions such as DesignWare functions from Synopsys and library of parameterized modules (LPM) functions automatically take advantage of carry chains for the appropriate functions.

The Quartus II Compiler creates carry chains longer than ten LEs by automatically linking LABs together. For enhanced fitting, a long carry chain skips alternate LABs in a MegaLAB structure. A carry chain longer than one LAB skips either from an even-numbered LAB to the next evennumbered LAB, or from an odd-numbered LAB to the next oddnumbered LAB. For example, the last LE of the first LAB in the upper-left MegaLAB structure carries to the first LE of the third LAB in the MegaLAB structure.

Figure 6 shows how an *n*-bit full adder can be implemented in n + 1 LEs with the carry chain. One portion of the LUT generates the sum of two bits using the input signals and the carry-in signal; the sum is routed to the output of the LE. The register can be bypassed for simple adders or used for accumulator functions. Another portion of the LUT and the carry chain logic generates the carry-out signal, which is routed directly to the carry-in signal of the next-higher-order bit. The final carry-out signal is routed to an LE, where it is driven onto the local, MegaLAB, or FastTrack interconnect routing structures.

The counter mode uses two 3-input LUTs: one generates the counter data, and the other generates the fast carry bit. A 2-to-1 multiplexer provides synchronous loading, and another AND gate provides synchronous clearing. If the cascade function is used by an LE in counter mode, the synchronous clear or load overrides any signal carried on the cascade chain. The synchronous clear overrides the synchronous load. LEs in arithmetic mode can drive out registered and unregistered versions of the LUT output.

## Clear & Preset Logic Control

Logic for the register's clear and preset signals is controlled by LAB-wide signals. The LE directly supports an asynchronous clear function. The Quartus II Compiler can use a NOT-gate push-back technique to emulate an asynchronous preset or to emulate simultaneous preset and clear or asynchronous load. However, this technique uses three additional LEs per register. All emulation is performed automatically when the design is compiled. Registers that emulate simultaneous preset and load will enter an unknown state upon power-up or when the chip-wide reset is asserted.

In addition to the two clear and preset modes, APEX 20KC devices provide a chip-wide reset pin (DEV\_CLRn) that resets all registers in the device. Use of this pin is controlled through an option in the Quartus II software that is set before compilation. The chip-wide reset overrides all other control signals. Registers using an asynchronous preset are preset when the chip-wide reset is asserted; this effect results from the inversion technique used to implement the asynchronous preset.

## FastTrack Interconnect

In the APEX 20KC architecture, connections between LEs, ESBs, and I/O pins are provided by the FastTrack interconnect. The FastTrack interconnect is a series of continuous horizontal and vertical routing channels that traverse the device. This global routing structure provides predictable performance, even in complex designs. In contrast, the segmented routing in FPGAs requires switch matrices to connect a variable number of routing paths, increasing the delays between logic resources and reducing performance.

The FastTrack interconnect consists of row and column interconnect channels that span the entire device. The row interconnect routes signals throughout a row of MegaLAB structures; the column interconnect routes signals throughout a column of MegaLAB structures. When using the row and column interconnect, an LE, IOE, or ESB can drive any other LE, IOE, or ESB in a device. See Figure 9.



Figure 9. APEX 20KC Interconnect Structure

A row line can be driven directly by LEs, IOEs, or ESBs in that row. Further, a column line can drive a row line, allowing an LE, IOE, or ESB to drive elements in a different row via the column and row interconnect. The row interconnect drives the MegaLAB interconnect to drive LEs, IOEs, or ESBs in a particular MegaLAB structure.

A column line can be directly driven by LEs, IOEs, or ESBs in that column. A column line on a device's left or right edge can also be driven by row IOEs. The column line is used to route signals from one row to another. A column line can drive a row line; it can also drive the MegaLAB interconnect directly, allowing faster connections between rows.

Figure 10 shows how the FastTrack interconnect uses the local interconnect to drive LEs within MegaLAB structures.

Table 8. AP	Table 8. APEX 20KC Routing Scheme								
Source					De	stination			
	Row I/O Pin	Column I/O Pin	LE	ESB	Local Interconnect	MegaLAB Interconnect	Row FastTrack Interconnect	Column FastTrack Interconnect	FastRow Interconnect
Row I/O pin					$\checkmark$	$\checkmark$	~	$\checkmark$	
Column I/O pin								~	~
LE					$\checkmark$	$\checkmark$	~	$\checkmark$	
ESB					<ul> <li>Image: A start of the start of</li></ul>	$\checkmark$	~	$\checkmark$	
Local interconnect	~	~	~	~					
MegaLAB interconnect					~				
Row FastTrack interconnect						~		~	
Column FastTrack interconnect						~	~		
FastRow interconnect					~				

## **Product-Term Logic**

The product-term portion of the MultiCore architecture is implemented with the ESB. The ESB can be configured to act as a block of macrocells on an ESB-by-ESB basis. Each ESB is fed by 32 inputs from the adjacent local interconnect; therefore, it can be driven by the MegaLAB interconnect or the adjacent LAB. Also, nine ESB macrocells feed back into the ESB through the local interconnect for higher performance. Dedicated clock pins, global signals, and additional inputs from the local interconnect drive the ESB control signals.

In product-term mode, each ESB contains 16 macrocells. Each macrocell consists of two product terms and a programmable register. Figure 13 shows the ESB in product-term mode.

ESBs can implement synchronous RAM, which is easier to use than asynchronous RAM. A circuit using asynchronous RAM must generate the RAM write enable (WE) signal, while ensuring that its data and address signals meet setup and hold time specifications relative to the WE signal. In contrast, the ESB's synchronous RAM generates its own WE signal and is self-timed with respect to the global clock. Circuits using the ESB's selftimed RAM must only meet the setup and hold time specifications of the global clock.

ESB inputs are driven by the adjacent local interconnect, which in turn can be driven by the FastTrack or MegaLAB interconnect. Because the ESB can be driven by the local interconnect, an adjacent LE can drive it directly for fast memory access. ESB outputs drive the FastTrack and MegaLAB interconnects. In addition, ten ESB outputs, nine of which are unique output lines, drive the local interconnect for fast connection to adjacent LEs or for fast feedback product-term logic.

When implementing memory, each ESB can be configured in any of the following sizes:  $128 \times 16$ ,  $256 \times 8$ ,  $512 \times 4$ ,  $1,024 \times 2$ , or  $2,048 \times 1$ . By combining multiple ESBs, the Quartus II software implements larger memory blocks automatically. For example, two  $128 \times 16$  RAM blocks can be combined to form a  $128 \times 32$  RAM block, and two  $512 \times 4$  RAM blocks can be combined to form a  $512 \times 8$  RAM block. Memory performance does not degrade for memory blocks up to 2,048 words deep. Each ESB can implement a 2,048-word-deep memory; the ESBs are used in parallel, eliminating the need for any external control logic and its associated delays.

To create a high-speed memory block that is more than 2,048 words deep, ESBs drive tri-state lines. Each tri-state line connects all ESBs in a column of MegaLAB structures, and drives the MegaLAB interconnect and row and column FastTrack interconnect throughout the column. Each ESB incorporates a programmable decoder to activate the tri-state driver appropriately. For instance, to implement 8,192-word-deep memory, four ESBs are used. Eleven address lines drive the ESB memory, and two more drive the tri-state decoder. Depending on which 2,048-word memory page is selected, the appropriate ESB driver is turned on, driving the output to the tri-state line. The Quartus II software automatically combines ESBs with tri-state lines to form deeper memory blocks. The internal tri-state control logic is designed to avoid internal contention and floating lines. See Figure 18.



#### Figure 23. APEX 20KC CAM Block Diagram

CAM can be used in any application requiring high-speed searches, such as networking, communications, data compression, and cache management.

The APEX 20KC on-chip CAM provides faster system performance than traditional discrete CAM. Integrating CAM and logic into the APEX 20KC device eliminates off-chip and on-chip delays, improving system performance.

When in CAM mode, the ESB implements 32-word, 32-bit CAM. Wider or deeper CAM can be implemented by combining multiple CAMs with some ancillary logic implemented in LEs. The Quartus II software combines ESBs and LEs automatically to create larger CAMs.

CAM supports writing "don't care" bits into words of the memory. The "don't care" bit can be used as a mask for CAM comparisons; any bit set to "don't care" has no effect on matches.

The output of the CAM can be encoded or unencoded. When encoded, the ESB outputs an encoded address of the data's location. For instance, if the data is located in address 12, the ESB output is 12. When unencoded, the ESB uses its 16 outputs to show the location of the data over two clock cycles. In this case, if the data is located in address 12, the 12th output line goes high. When using unencoded outputs, two clock cycles are required to read the output because a 16-bit output bus is used to show the status of 32 words.

The encoded output is better suited for designs that ensure duplicate data is not written into the CAM. If duplicate data is written into two locations, the CAM's output will be incorrect. If the CAM may contain duplicate data, the unencoded output is a better solution; CAM with unencoded outputs can distinguish multiple data locations.

CAM can be pre-loaded with data during configuration, or it can be written during system operation. In most cases, two clock cycles are required to write each word into CAM. When "don't care" bits are used, a third clock cycle is required.



For more information on APEX 20KC devices and CAM, see *Application* Note 119 (Implementing High-Speed Search Applications with APEX CAM).

## Driving Signals to the ESB

ESBs provide flexible options for driving control signals. Different clocks can be used for the ESB inputs and outputs. Registers can be inserted independently on the data input, data output, read address, write address, WE, and RE signals. The global signals and the local interconnect can drive the WE and RE signals. The global signals, dedicated clock pins, and local interconnect can drive the ESB clock signals. Because the LEs drive the local interconnect, the LEs can control the WE and RE signals and the ESB clock, clock enable, and asynchronous clear signals. Figure 24 shows the ESB control signal generation logic.

Figure 24. ESB Control Signal Generation



An ESB is fed by the local interconnect, which is driven by adjacent LEs (for high-speed connection to the ESB) or the MegaLAB interconnect. The ESB can drive the local, MegaLAB, or FastTrack interconnect routing structure to drive LEs and IOEs in the same MegaLAB structure or anywhere in the device.

## Implementing Logic in ROM

In addition to implementing logic with product terms, the ESB can implement logic functions when it is programmed with a read-only pattern during configuration, creating a large LUT. With LUTs, combinatorial functions are implemented by looking up the results, rather than by computing them. This implementation of combinatorial functions can be faster than using algorithms implemented in general logic, a performance advantage that is further enhanced by the fast access times of ESBs. The large capacity of ESBs enables designers to implement complex functions in one logic level without the routing delays associated with linked LEs or distributed RAM blocks. Parameterized functions such as LPM functions can take advantage of the ESB automatically. Further, the Quartus II software can implement portions of a design with ESBs where appropriate.

## **Programmable Speed/Power Control**

APEX 20KC ESBs offer a high-speed mode that supports very fast operation on an ESB-by-ESB basis. When high speed is not required, this feature can be turned off to reduce the ESB's power dissipation by up to 50%. ESBs that run at low power incur a nominal timing delay adder. This Turbo Bit<sup>™</sup> option is available for ESBs that implement product-term logic or memory functions. An ESB that is not used will be powered down so that it does not consume DC current.

Designers can program each ESB in the APEX 20KC device for either high-speed or low-power operation. As a result, speed-critical paths in the design can run at high speed, while the remaining paths operate at reduced power.

# I/O Structure

The APEX 20KC IOE contains a bidirectional I/O buffer and a register that can be used either as an input register for external data requiring fast setup times or as an output register for data requiring fast clock-to-output performance. IOEs can be used as input, output, or bidirectional pins. The register in the APEX 20KC IOE can be programmed to power-up high or low after configuration is complete. If it is programmed to power-up low, an asynchronous clear can control the register. If it is programmed to power-up high, an asynchronous preset can control the register. This feature is useful for cases where the APEX 20KC device controls an activelow input or another device; it prevents inadvertent activation of the input upon power-up.

Figure 25 shows how fast bidirectional I/O pins are implemented in APEX 20KC devices. This feature is useful for cases where the APEX 20KC device controls an active-low input or another device; it prevents inadvertent activation of the input upon power-up.

## Clock Multiplication

The APEX 20KC ClockBoost circuit can multiply or divide clocks by a programmable number. The clock can be multiplied by  $m/(n \times k)$ , where m and k range from 2 to 160 and n ranges from 1 to 16. Clock multiplication and division can be used for time-domain multiplexing and other functions, which can reduce design LE requirements.

## Clock Phase & Delay Adjustment

The APEX 20KC ClockShift feature allows the clock phase and delay to be adjusted. The clock phase can be adjusted by 90° steps. The clock delay can be adjusted to increase or decrease the clock delay by an arbitrary amount, up to one clock period.

## LVDS Support

All APEX 20KC devices support differential LVDS buffers on the input and output clock signals that interface with external devices. This is controlled in the Quartus II software by assigning the clock pins with an LVDS I/O standard assignment.

Two high-speed PLLs are designed to support the LVDS interface. When using LVDS, the I/O clock runs at a slower rate than the data transfer rate. Thus, PLLs are used to multiply the I/O clock internally to capture the LVDS data. For example, an I/O clock may run at 105 MHz to support 840 Mbps LVDS data transfer. In this example, the PLL multiplies the incoming clock by eight to support the high-speed data transfer. You can use PLLs in EP20K400C and larger devices for high-speed LVDS interfacing.

## Lock Signals

The APEX 20KC ClockLock circuitry supports individual LOCK signals. The LOCK signal drives high when the ClockLock circuit has locked onto the input clock. The LOCK signals are optional for each ClockLock circuit; when not used, they are I/O pins.

Table 12. APEX 20KC Clock Input & Output Parameters (Part 2 of 2)       Note (1)							
Symbol	Parameter	I/O Standard	-7 Spee	ed Grade	-8 Spee	ed Grade	Units
			Min	Max	Min	Max	
f <sub>CLOCK1_EXT</sub>	Output clock frequency for	3.3-V LVTTL	(5)	(5)	(5)	(5)	MHz
	external clock1 output	2.5-V LVTTL	(5)	(5)	(5)	(5)	MHz
		1.8-V LVTTL	(5)	(5)	(5)	(5)	MHz
		GTL+	(5)	(5)	(5)	(5)	MHz
		SSTL-2 Class I	(5)	(5)	(5)	(5)	MHz
		SSTL-2 Class II	(5)	(5)	(5)	(5)	MHz
		SSTL-3 Class I	(5)	(5)	(5)	(5)	MHz
		SSTL-3 Class II	(5)	(5)	(5)	(5)	MHz
		LVDS	(5)	(5)	(5)	(5)	MHz
f <sub>IN</sub>	Input clock frequency	3.3-V LVTTL	(5)	(5)	(5)	(5)	MHz
		2.5-V LVTTL	(5)	(5)	(5)	(5)	MHz
		1.8-V LVTTL	(5)	(5)	(5)	(5)	MHz
		GTL+	(5)	(5)	(5)	(5)	MHz
		SSTL-2 Class I	(5)	(5)	(5)	(5)	MHz
		SSTL-2 Class II	(5)	(5)	(5)	(5)	MHz
		SSTL-3 Class I	(5)	(5)	(5)	(5)	MHz
		SSTL-3 Class II	(5)	(5)	(5)	(5)	MHz
		LVDS	(5)	(5)	(5)	(5)	MHz

#### Notes to Tables 11 and 12:

- (1) All input clock specifications must be met. The PLL may not lock onto an incoming clock if the clock specifications are not met, creating an erroneous clock within the device.
- (2) The maximum lock time is 40 µs or 2,000 input clock cycles, whichever occurs first.
- (3) Before configuration, the PLL circuits are disable and powered down. During configuration, the PLLs remain disabled. The PLLs begin to lock once the device is in the user mode. If the clock enable feature is used, lock begins once the CLKLK\_ENA pin goes high in user mode.
- (4) The PLL VCO operating range is 200 MHz  $\leq f_{VCO} \leq$  840 MHz for LVDS mode.

(5) Contact Altera Applications for information on these parameters.

# SignalTap Embedded Logic Analyzer

APEX 20KC devices include device enhancements to support the SignalTap embedded logic analyzer. By including this circuitry, the APEX 20KC device provides the ability to monitor design operation over a period of time through the IEEE Std. 1149.1 (JTAG) circuitry; a designer can analyze internal logic at speed without bringing internal signals to the I/O pins. This feature is particularly important for advanced packages such as FineLine BGA packages because adding a connection to a pin during the debugging process can be difficult after a board is designed and manufactured.

Table 22. LVCMOS I/O Specifications						
Symbol	Parameter	Conditions	Minimum	Maximum	Units	
V <sub>CCIO</sub>	Power supply voltage range		3.0	3.6	V	
V <sub>IH</sub>	High-level input voltage		2.0	V <sub>CCIO</sub> + 0.3	V	
V <sub>IL</sub>	Low-level input voltage		-0.3	0.8	V	
I <sub>I</sub>	Input pin leakage current	V <sub>IN</sub> = 0 V or 3.3 V	-10	10	μA	
V <sub>OH</sub>	High-level output voltage	V <sub>CCIO</sub> = 3.0 V I <sub>OH</sub> = -0.1 mA (1)	V <sub>CCIO</sub> – 0.2		V	
V <sub>OL</sub>	Low-level output voltage	V <sub>CCIO</sub> = 3.0 V I <sub>OL</sub> = 0.1 mA <i>(2)</i>		0.2	V	

Table 23. 2.5-V I/O Specifications						
Symbol	Parameter	Conditions	Minimum	Maximum	Units	
V <sub>CCIO</sub>	Output supply voltage		2.375	2.625	V	
V <sub>IH</sub>	High-level input voltage		1.7	V <sub>CCIO</sub> + 0.3	V	
V <sub>IL</sub>	Low-level input voltage		-0.3	0.8	V	
I <sub>I</sub>	Input pin leakage current	V <sub>IN</sub> = 0 V or 3.3 V	-10	10	μA	
V <sub>OH</sub>	High-level output	I <sub>OH</sub> = -0.1 mA (1)	2.1		V	
	voltage	I <sub>OH</sub> = -1 mA (1)	2.0		V	
		$I_{OH} = -2 \text{ mA} (1)$	1.7		V	
V <sub>OL</sub>	Low-level output	I <sub>OL</sub> = 0.1 mA <i>(2)</i>		0.2	V	
	voltage	I <sub>OL</sub> = 1 mA <i>(2)</i>		0.4	V	
		I <sub>OL</sub> = 2 mA <i>(2)</i>		0.7	V	

Table 30. SSTL-2 Class II Specifications						
Symbol	Parameter	Conditions	Minimum	Typical	Maximum	Units
V <sub>CCIO</sub>	I/O supply voltage		2.375	2.5	2.625	V
V <sub>TT</sub>	Termination voltage		V <sub>REF</sub> - 0.04	V <sub>REF</sub>	V <sub>REF</sub> + 0.04	V
V <sub>REF</sub>	Reference voltage		1.15	1.25	1.35	V
V <sub>IH</sub>	High-level input voltage		V <sub>REF</sub> + 0.18		V <sub>CCIO</sub> + 0.3	V
V <sub>IL</sub>	Low-level input voltage		-0.3		V <sub>REF</sub> - 0.18	V
V <sub>OH</sub>	High-level output voltage	I <sub>OH</sub> = -15.2 mA <i>(1)</i>	V <sub>TT</sub> + 0.76			V
V <sub>OL</sub>	Low-level output voltage	I <sub>OL</sub> = 15.2 mA <i>(2)</i>			V <sub>TT</sub> – 0.76	V

Table 31.	SSTL-3 (	Class I	Specifications
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Symbol	Parameter	Conditions	Minimum	Typical	Maximum	Units
V <sub>CCIO</sub>	I/O supply voltage		3.0	3.3	3.6	V
V <sub>TT</sub>	Termination voltage		$V_{REF} - 0.05$	$V_{REF}$	V <sub>REF</sub> + 0.05	V
V <sub>REF</sub>	Reference voltage		1.3	1.5	1.7	V
V <sub>IH</sub>	High-level input voltage		V <sub>REF</sub> + 0.2		V <sub>CCIO</sub> + 0.3	V
V <sub>IL</sub>	Low-level input voltage		-0.3		V <sub>REF</sub> - 0.2	V
V <sub>OH</sub>	High-level output voltage	I <sub>OH</sub> = -8 mA (1)	V <sub>TT</sub> + 0.6			V
V <sub>OL</sub>	Low-level output voltage	I <sub>OL</sub> = 8 mA (2)			V <sub>TT</sub> – 0.6	V

Table 32. SSTL-3 Class II Specifications						
Symbol	Parameter	Conditions	Minimum	Typical	Maximum	Units
V <sub>CCIO</sub>	I/O supply voltage		3.0	3.3	3.6	V
V <sub>TT</sub>	Termination voltage		V <sub>REF</sub> - 0.05	V <sub>REF</sub>	V <sub>REF</sub> + 0.05	V
V <sub>REF</sub>	Reference voltage		1.3	1.5	1.7	V
V <sub>IH</sub>	High-level input voltage		V <sub>REF</sub> + 0.2		V <sub>CCIO</sub> + 0.3	V
V <sub>IL</sub>	Low-level input voltage		-0.3		V <sub>REF</sub> - 0.2	V
V <sub>OH</sub>	High-level output voltage	I <sub>OH</sub> = -16 mA (1)	V <sub>TT</sub> + 0.8			V
V <sub>OL</sub>	Low-level output voltage	I <sub>OL</sub> = 16 mA <i>(2)</i>			V <sub>TT</sub> – 0.8	V

Table 33. HSTL Class I I/O Specifications						
Symbol	Parameter	Conditions	Minimum	Typical	Maximum	Units
V <sub>CCIO</sub>	I/O supply voltage		1.71	1.8	1.89	V
V <sub>TT</sub>	Termination voltage		$V_{REF} - 0.05$	V <sub>REF</sub>	V <sub>REF</sub> + 0.05	V
V <sub>REF</sub>	Reference voltage		0.68	0.75	0.90	V
V <sub>IH</sub>	High-level input voltage		V <sub>REF</sub> + 0.1		V <sub>CCIO</sub> + 0.3	V
V <sub>IL</sub>	Low-level input voltage		-0.3		V <sub>REF</sub> – 0.1	V
V <sub>OH</sub>	High-level output voltage	I <sub>OH</sub> = -8 mA (1)	V <sub>CCIO</sub> – 0.4			V
V <sub>OL</sub>	Low-level output voltage	I <sub>OL</sub> = 8 mA (2)			0.4	V

## **Altera Corporation**

Table 37. APEX 20KC f <sub>MAX</sub> ESB Timing Parameters					

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Symbol	Parameter			
t <sub>ESBARC</sub>	ESB asynchronous read cycle time			
t <sub>ESBSRC</sub>	ESB synchronous read cycle time			
t <sub>ESBAWC</sub>	ESB asynchronous write cycle time			
t <sub>ESBSWC</sub>	ESB synchronous write cycle time			
t <sub>ESBWASU</sub>	ESB write address setup time with respect to WE			
t <sub>ESBWAH</sub>	ESB write address hold time with respect to WE			
t <sub>ESBWDSU</sub>	ESB data setup time with respect to WE			
t <sub>ESBWDH</sub>	ESB data hold time with respect to WE			
t <sub>ESBRASU</sub>	ESB read address setup time with respect to RE			
t <sub>ESBRAH</sub>	ESB read address hold time with respect to RE			
t <sub>ESBWESU</sub>	ESB WE setup time before clock when using input register			
t <sub>ESBDATASU</sub>	ESB data setup time before clock when using input register			
t <sub>ESBWADDRSU</sub>	ESB write address setup time before clock when using input registers			
t <sub>ESBRADDRSU</sub>	ESB read address setup time before clock when using input registers			
t <sub>ESBDATACO1</sub>	ESB clock-to-output delay when using output registers			
t <sub>ESBDATACO2</sub>	ESB clock-to-output delay without output registers			
t <sub>ESBDD</sub>	ESB data-in to data-out delay for RAM mode			
t <sub>PD</sub>	ESB macrocell input to non-registered output			
t <sub>PTERMSU</sub>	ESB macrocell register setup time before clock			
t <sub>PTERMCO</sub>	ESB macrocell register clock-to-output delay			

## Table 38. APEX 20KC f<sub>MAX</sub> Routing Delays

Symbol	Parameter
t <sub>F1-4</sub>	Fan-out delay estimate using local interconnect
t <sub>F5-20</sub>	Fan-out delay estimate using MegaLab interconnect
t <sub>F20+</sub>	Fan-out delay estimate using FastTrack interconnect

Figure 36. AC Test Conditions for LVTTL, 2.5 V, 1.8 V, PCI & GTL+ I/O Standards











Table 46. EP20K200C f <sub>MAX</sub> Routing Delays										
Symbol	-7 Spee	ed Grade	-8 Speed Grade		-9 Speed Grade		Unit			
	Min	Max	Min	Max	Min	Max				
t <sub>F1-4</sub>		0.15		0.17		0.20	ns			
t <sub>F5-20</sub>		0.81		0.94		1.12	ns			
t <sub>F20+</sub>		0.98		1.13		1.35	ns			

Table 47. EP20K200C Minimum Pulse Width Timing Parameters										
Symbol	-7 Spee	d Grade	-8 Spee	d Grade	-9 Spee	Unit				
	Min	Max	Min	Max	Min	Max				
t <sub>CH</sub>	1.33		1.66		2.00		ns			
t <sub>CL</sub>	1.33		1.66		2.00		ns			
t <sub>CLRP</sub>	0.20		0.20		0.20		ns			
t <sub>PREP</sub>	0.20		0.20		0.20		ns			
t <sub>ESBCH</sub>	1.33		1.66		2.00		ns			
t <sub>ESBCL</sub>	1.33		1.66		2.00		ns			
t <sub>ESBWP</sub>	1.05		1.28		1.44		ns			
t <sub>ESBRP</sub>	0.87		1.06		1.19		ns			

## Table 48. EP20K200C External Timing Parameters

Symbol	-7 Speed Grade		-8 Spe	ed Grade	-9 Spee	Unit	
	Min	Max	Min	Max	Min	Max	
t <sub>INSU</sub>	1.23		1.26		1.33		ns
t <sub>INH</sub>	0.00		0.00		0.00		ns
t <sub>оитсо</sub>	2.00	3.79	2.00	4.31	2.00	4.70	ns
t <sub>INSUPLL</sub>	0.81		0.92		-		ns
t <sub>INHPLL</sub>	0.00		0.00		-		ns
t <sub>OUTCOPLL</sub>	0.50	2.36	0.50	2.62	-	-	ns

Table 53. EP20K400C Minimum Pulse Width Timing Parameters										
Symbol	-7 Spee	d Grade	-8 Spee	d Grade	-9 Spee	d Grade	Unit			
	Min	Max	Min	Max	Min	Max				
t <sub>CH</sub>	1.33		1.66		2.00		ns			
t <sub>CL</sub>	1.33		1.66		2.00		ns			
t <sub>CLRP</sub>	0.20		0.20		0.20		ns			
t <sub>PREP</sub>	0.20		0.20		0.20		ns			
t <sub>ESBCH</sub>	1.33		1.66		2.00		ns			
t <sub>ESBCL</sub>	1.33		1.66		2.00		ns			
t <sub>ESBWP</sub>	1.05		1.28		1.44		ns			
t <sub>ESBRP</sub>	0.87		1.06		1.19		ns			

Table 54. EP20K400C External Timing Parameters											
Symbol	-7 Speed Grade		-8 Spee	-8 Speed Grade		-9 Speed Grade					
	Min	Max	Min	Max	Min	Max					
t <sub>INSU</sub>	1.37		1.52		1.64		ns				
t <sub>INH</sub>	0.00		0.00		0.00		ns				
t <sub>оитсо</sub>	2.00	4.25	2.00	4.61	2.00	5.03	ns				
t <sub>INSUPLL</sub>	0.80		0.91		-		ns				
tINHPLL	0.00		0.00		-		ns				
t <sub>OUTCOPLL</sub>	0.50	2.27	0.50	2.55	-	-	ns				

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Table 55. EP20K400C External Bidirectional Timing Parameters											
Symbol	-7 Spec	ed Grade	-8 Spee	ed Grade	-9 Spec	ed Grade	Unit				
	Min	Max	Min	Max	Min	Max					
t <sub>INSUBIDIR</sub>	1.29		1.67		1.92		ns				
t <sub>INHBIDIR</sub>	0.00		0.00		0.00		ns				
t <sub>OUTCOBIDIR</sub>	2.00	4.25	2.00	4.61	2.00	5.03	ns				
t <sub>XZBIDIR</sub>		6.55		6.97		7.35	ns				
t <sub>ZXBIDIR</sub>		6.55		6.97		7.36	ns				
t <sub>INSUBIDIRPLL</sub>	3.22		3.80		-		ns				
t <sub>INHBIDIRPLL</sub>	0.00		0.00		-		ns				
t <sub>OUTCOBIDIRPLL</sub>	0.50	2.27	0.50	2.55	-	-	ns				
tXZBIDIRPLL		4.62		4.84		-	ns				
t <sub>ZXBIDIRPLL</sub>		4.62		4.84		-	ns				

Table 56. EP20K600C f <sub>MAX</sub> LE Timing Parameters									
Symbol	-7 Spee	ed Grade	-8 Spee	d Grade	-9 Spee	Unit			
	Min	Max	Min	Max	Min	Max			
t <sub>SU</sub>	0.01		0.01		0.01		ns		
t <sub>H</sub>	0.10		0.10		0.10		ns		
t <sub>CO</sub>		0.27		0.30		0.32	ns		
t <sub>LUT</sub>		0.65		0.78		0.92	ns		

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